General Purpose Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	Ic	200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

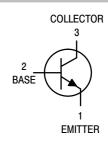
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

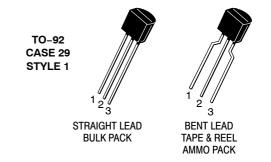
1. Indicates Data in addition to JEDEC Requirements.



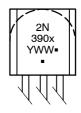
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAMS



x = 3 or 4

Y = Year

WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

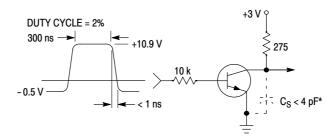
	Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTER	RISTICS				•	•
Collector - Emitter	Breakdown Voltage (Note 2) ($I_C = 1.0 \text{ mAdc}, I_B = 0$))	V _{(BR)CEO}	40	-	Vdc
Collector - Base Br	reakdown Voltage (I _C = 10 μAdc, I _E = 0)		V _{(BR)CBO}	60	-	Vdc
Emitter-Base Brea	akdown Voltage (I _E = 10 μAdc, I _C = 0)		V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Currer	nt (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{BL}	_	50	nAdc
Collector Cutoff Cu	urrent (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{CEX}	-	50	nAdc
ON CHARACTERI	ISTICS			1	<u>'</u>	
DC Current Gain (I _C = 0.1 mAdc, V _C		2N3903	h _{FE}	20	_	-
$(I_C = 1.0 \text{ mAdc}, V_C)$	_{DE} = 1.0 Vdc)	2N3904 2N3903 2N3904		40 35 70	- - -	
$(I_C = 10 \text{ mAdc}, V_C)$	_E = 1.0 Vdc)	2N3903		50	150	
(I _C = 50 mAdc, V _C	_E = 1.0 Vdc)	2N3904 2N3903		100 30	300	
(I _C = 100 mAdc, V ₀		2N3904 2N3903		60 15		
(10 - 100 11) (40, 7)	GE = 1.0 vao)	2N3904		30	_	
Collector – Emitter Saturation Voltage (Note 2) (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 50 mAdc, I _B = 5.0 mAdc		V _{CE(sat)}	_ _	0.2 0.3	Vdc	
Base – Emitter Saturation Voltage (Note 2) (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 50 mAdc, I _B = 5.0 mAdc)			V _{BE(sat)}	0.65	0.85 0.95	Vdc
•	CHARACTERISTICS			<u> </u>		
Current – Gain – Ba (I _C = 10 mAdc, V _C	andwidth Product E = 20 Vdc, f = 100 MHz)	2N3903 2N3904	f _T	250 300	- -	MHz
Output Capacitano	ce (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	_	4.0	pF
Input Capacitance	(V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	_	8.0	pF
Input Impedance	_{DE} = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{ie}	1.0 1.0	8.0 10	kΩ
Voltage Feedback Ratio (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		2N3903 2N3904	h _{re}	0.1 0.5	5.0 8.0	X 10 ⁻⁴
Small-Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		2N3903 2N3904	h _{fe}	50 100	200 400	-
Output Admittance	e (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{oe}	1.0	40	μmhos
Noise Figure (I _C = 100 μAdc, V _C	$\Omega_{\rm E}$ = 5.0 Vdc, R _S = 1.0 k Ω, f = 1.0 kHz)	2N3903 2N3904	NF	- -	6.0 5.0	dB
SWITCHING CHA	RACTERISTICS					•
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = 0.5 Vdc,		t _d	-	35	ns
Rise Time	I _C = 10 mAdc, I _{B1} = 1.0 mAdc)		t _r	-	35	ns
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}, I_C = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	2N3903 2N3904	t _s	- -	175 200	ns
Fall Time			t _f	_	50	ns

^{2.} Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2%.

ORDERING INFORMATION

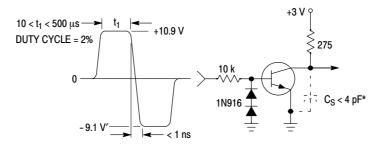
Device	Package	Shipping [†]
2N3903RLRM	TO-92	2000 / Ammo Pack
2N3904	TO-92	5000 Units / Bulk
2N3904G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3904RLRA	TO-92	2000 / Tape & Reel
2N3904RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904RLRM	TO-92	2000 / Ammo Pack
2N3904RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RLRP	TO-92	2000 / Ammo Pack
2N3904RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904ZL1	TO-92	2000 / Ammo Pack
2N3904ZL1G	TO-92 (Pb-Free)	2000 / Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



* Total shunt capacitance of test jig and connectors

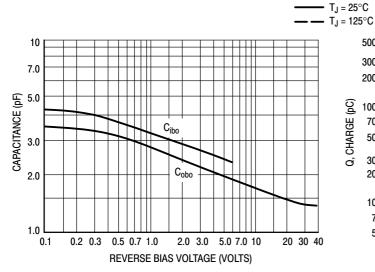
Figure 1. Delay and Rise Time Equivalent Test Circuit



* Total shunt capacitance of test jig and connectors

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS



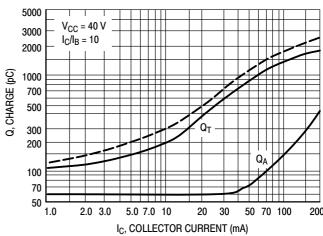
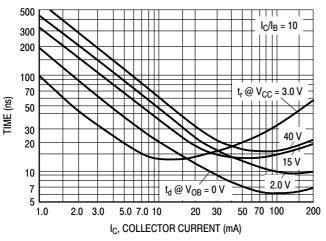


Figure 3. Capacitance

Figure 4. Charge Data



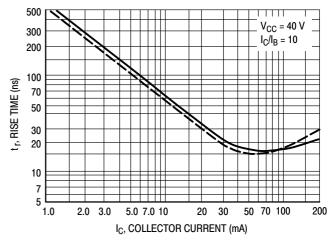
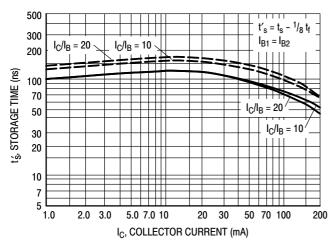


Figure 5. Turn-On Time

Figure 6. Rise Time



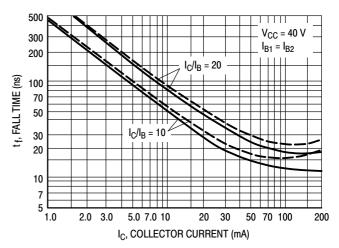
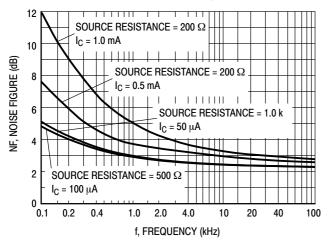


Figure 7. Storage Time

Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



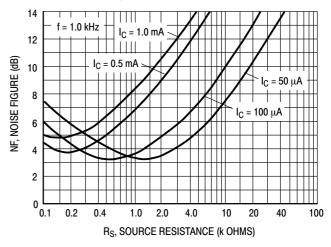
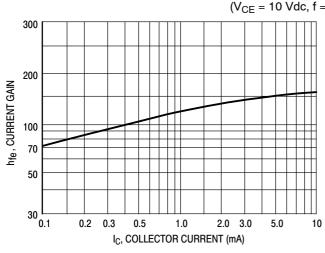


Figure 9.

Figure 10.

h PARAMETERS



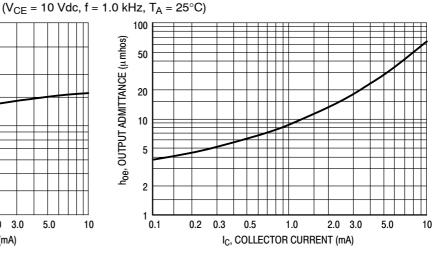
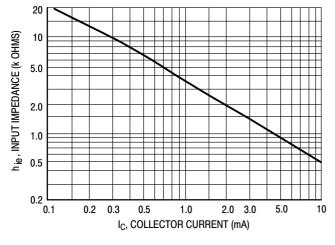


Figure 11. Current Gain

Figure 12. Output Admittance



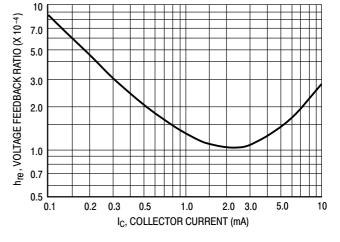


Figure 13. Input Impedance

Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

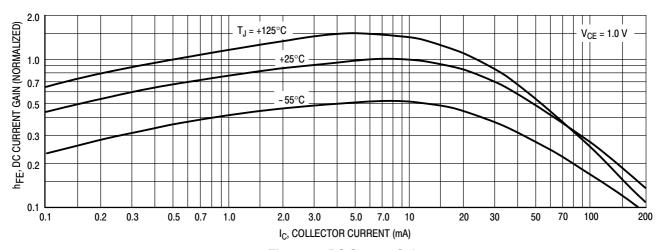


Figure 15. DC Current Gain

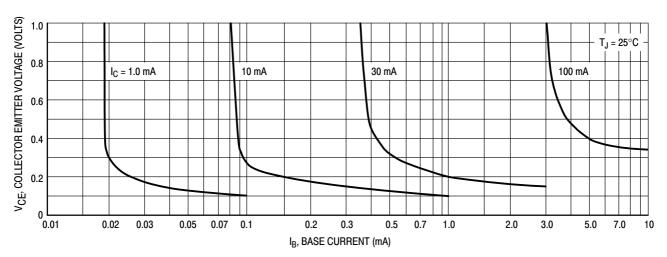


Figure 16. Collector Saturation Region

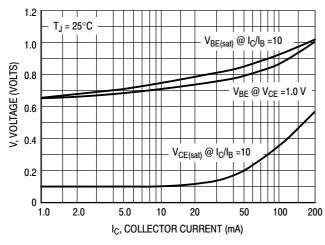


Figure 17. "ON" Voltages

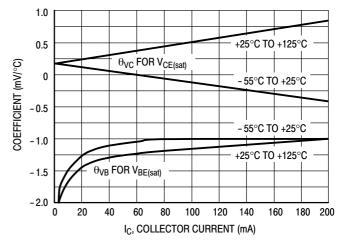
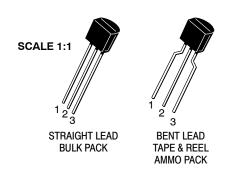


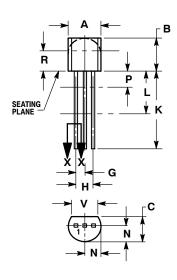
Figure 18. Temperature Coefficients





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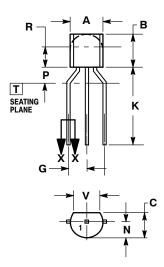


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS					
DIM	MIN	MAX				
Α	4.45	5.20				
В	4.32	5.33				
С	3.18	4.19				
D	0.40	0.54				
G	2.40	2.80				
J	0.39	0.50				
K	12.70					
N	2.04	2.66				
P	1.50	4.00				
R	2.93					
V	3.43					

STYLES ON PAGE 2

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TO-92 (TO-226) CASE 29-11

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DATE 09 MAR 2007

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN
2.	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	PIN 1.	BASE 1		CATHODE
2.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	PIN 1.	ANODE 1	PIN 1.	EMITTER COLLECTOR BASE	PIN 1. 2.	
2.	ANODE GATE	PIN 1. 2.	COLLECTOR BASE	PIN 1. 2.	ANODE CATHODE	PIN 1. 2.	GATE	2.	NOT CONNECTED
2.	COLLECTOR	PIN 1. 2.	SOURCE GATE DRAIN	STYLE 23: PIN 1. 2. 3.	GATE SOURCE DRAIN	STYLE 24: PIN 1. 2. 3.	EMITTER COLLECTOR/ANODE CATHODE	STYLE 25: PIN 1. 2. 3.	MT 1 GATE
	V _{CC}	PIN 1. 2.	MT	STYLE 28: PIN 1. 2.	CATHODE ANODE GATE	STYLE 29: PIN 1. 2.		PIN 1. 2.	DRAIN
	GATE	PIN 1. 2.		STYLE 33: PIN 1. 2. 3.	RETURN	2.			

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